TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

# 2SK3403

## **Switching Regulator Applications**

- Low drain-source ON-resistance:  $R_{DS (ON)} = 0.29 \Omega$  (typ.)
- High forward transfer admittance: |Y<sub>fs</sub>| = 5.8 S (typ.)
- Low leakage current: I<sub>DSS</sub> = 100 μA (max) (V<sub>DS</sub> = 450 V)
- Enhancement mode:  $V_{th}$  = 3.0 to 5.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

# Absolute Maximum Ratings (Ta = 25°C)

| Characteristics                                      |       | Symbol   | Rating               | Unit       |       |
|--|-------|----------|----------------------|------------|-------|
| Drain-source voltage                                 |       |          | $V_{DSS}$            | 450        | (y)   |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ ) |       |          | $V_{DGR}$            | 450        | (     |
| Gate-source voltage                                  |       |          | $V_{GSS}$            | ±30        | V     |
| Drain current  | DC    | (Note 1) | ΙD                   | 13         | A     |
|  | Pulse | (Note 1) | $I_{DP}$             | 52         | ∧     |
| Drain power dissipation (Tc = 25°C)                  |       |          | $P_{D}$              | 100        | W     |
| Single pulse avalanche energy (Note 2)               |       |          | E <sub>AS</sub>      | 350        | mJ    |
| Avalanche current                                    |       |          | IAR                  | 13         | A     |
| Repetitive avalanche energy (Note 3)                 |       |          | EAR                  | )) 10      | mJ    |
| Channel temperature                                  |       |          | Teh                  | 150        | √ °C  |
| Storage temperature range                            |       |          | (T <sub>stg</sub> )) | -55 to 150 | _//°C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions") "Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### Thermal Characteristics

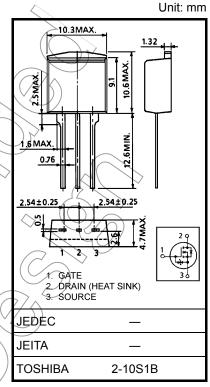
| Characteristics                        | Symbol                 | Max  | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 1.25 | °C/W |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 83.3 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

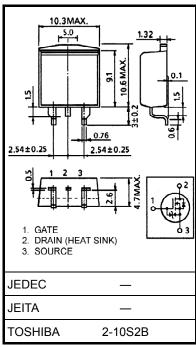
Note 2:  $V_{DD} = 90 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial), L = 3.46 mH,  $R_G = 25 \Omega$ ,  $L_{AD} = 13 \text{ A}$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.



Weight: 1.5 g (typ.)



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### **Electrical Characteristics (Tc = 25°C)**

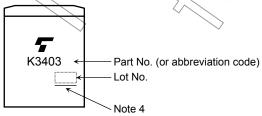
| Characteristics              |                                    | Symbol               | Test Condition  | Min      | Тур. | Max                                    | Unit |
|------------------------------|------------------------------------|----------------------|---|----------|------|--|------|
| Gate leakage cur             | rent                               | I <sub>GSS</sub>     | $V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$                           | _        | _    | ±10                                    | μΑ   |
| Gate-source brea             | kdown voltage                      | V (BR) GSS           | $I_G = \pm 10 \ \mu A, \ V_{DS} = 0 \ V$                                    | ±30      | _    |  | V    |
| Drain cut-off curre          | ent                                | I <sub>DSS</sub>     | V <sub>DS</sub> = 450 V, V <sub>GS</sub> = 0 V                              |          | _    | 100                                    | μА   |
| Drain-source brea            | ain-source breakdown voltage V (BF |                      | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$                                 | 450      | _    | _                                      | V    |
| Gate threshold vo            | oltage                             | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA                               | 3.0      | ) >_ | 5.0                                    | V    |
| Drain-source ON-resistance   |                                    | R <sub>DS (ON)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6 A                                |          | 0.29 | 0.4                                    | Ω    |
| Forward transfer             | admittance                         | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 6 A                                | 3.0      | 5.8  | _                                      | S    |
| Input capacitance            |                                    | C <sub>iss</sub>     |   | _        | 1600 | _                                      |      |
| Reverse transfer capacitance |                                    | C <sub>rss</sub>     | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz                    | <i>_</i> | 17   | _                                      | pF   |
| Output capacitan             | Output capacitance                 |                      |   | _        | 220  | _                                      |      |
| Switching time               | Rise time                          | t <sub>r</sub>       | VGS D=6A Output   | - (      | 28   | \\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ |      |
|                              | Turn-on time                       | t <sub>on</sub>      | 0 V J RI =  |          | 45   | ) _                                    |      |
|                              | Fall time                          | t <sub>f</sub>       | 33.3 Ω<br>V <sub>DD</sub> ≈ 200 V   | 7        | 10   |  | ns   |
|                              | Turn-off time                      | t <sub>off</sub>     | Duty $\leq$ 1%, t <sub>w</sub> = 10 µs                                      | ) —      | 56   |  |      |
| Total gate charge Qg         |                                    | Qg                   |   |          | 34   | _                                      |      |
| Gate-source charge           |                                    | Q <sub>g\$</sub>     | $V_{DD} \approx 360 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 13 \text{ A}$ |          | 19   | _                                      | nC   |
| Gate-drain charge            |                                    | Qgd                  |   | _        | 15   | _                                      |      |

# Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol          | Test Condition                                 | Min | Тур. | Max  | Unit |
|---|-----------------|--|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub> |  | _   | _    | 13   | Α    |
| Pulse drain reverse current (Note 1)      | IDRP            | _  | _   | _    | 52   | Α    |
| Forward voltage (diode)                   | VDSF            | I <sub>DR</sub> = 13 A, V <sub>GS</sub> = 0 V  | _   | _    | -1.7 | V    |
| Reverse recovery time                     | t <sub>rr</sub> | 1 <sub>DR</sub> = 13 A, V <sub>GS</sub> = 0 V, | _   | 300  | _    | ns   |
| Reverse recovery charge                   | Qrr             | dI <sub>DR</sub> /dt = 100 A/μs                | _   | 3.4  | _    | μС   |

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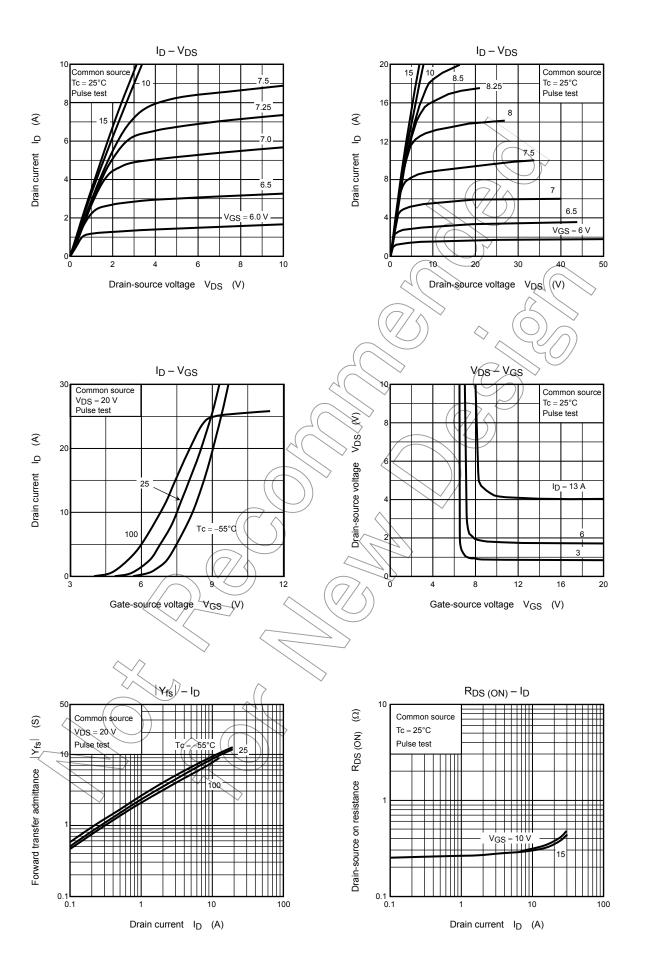


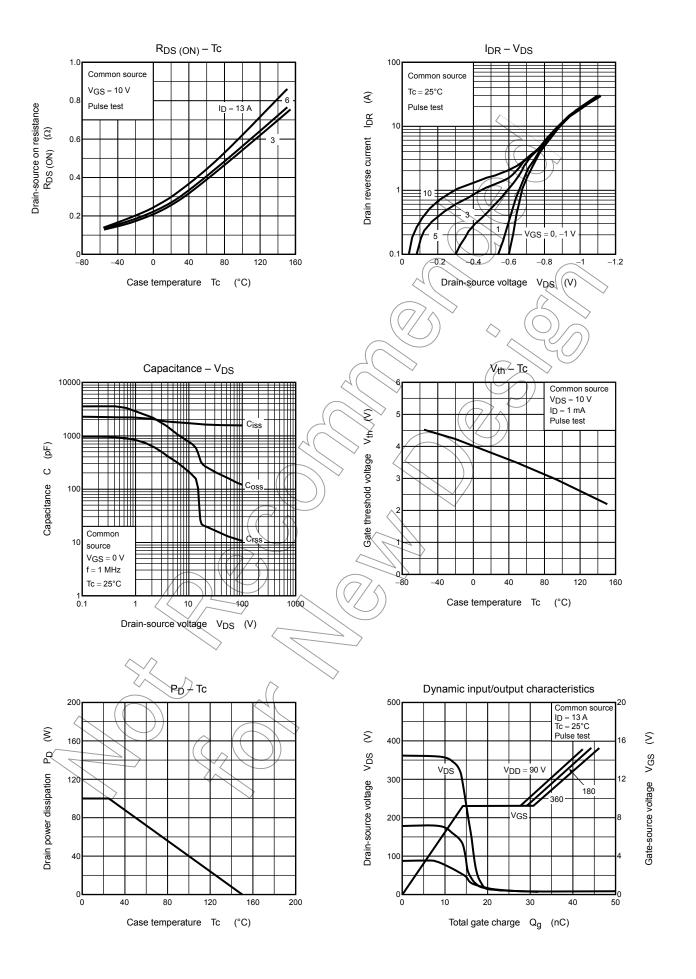
Note 4: A line under a Lot No. identifies the indication of product Labels.

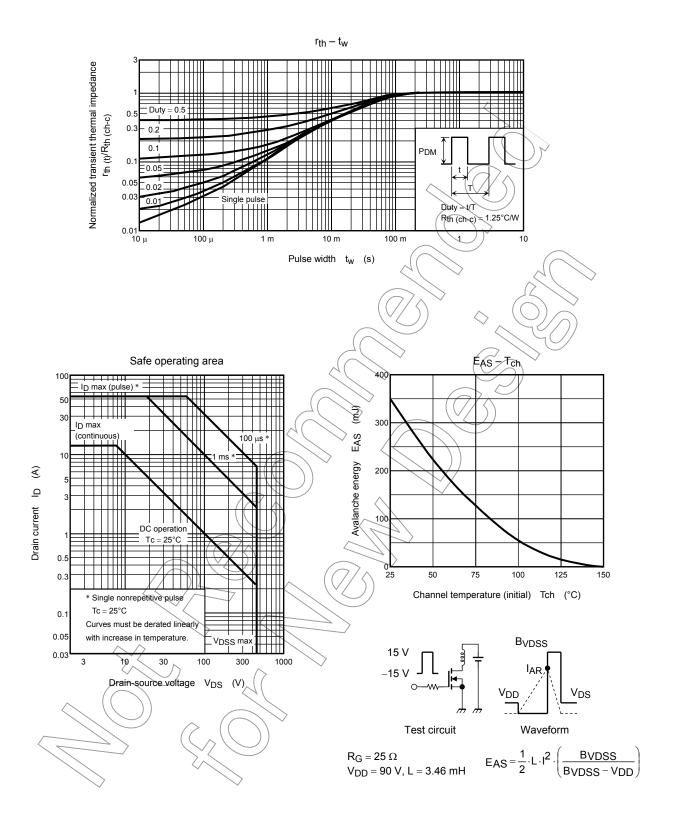
Not underlined: [[Pb]]/INCLUDES > MCV

 $\label{thm:compatible} \mbox{Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]}$ 

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5 2010-04-13

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